

SEMICONDUCTOR

November 2013

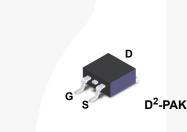
FQB11P06 P-Channel QFET® MOSFET -60 V, -11.4 A, 175 mΩ

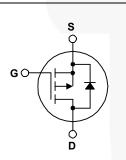
Description

This P-Channel enhancement mode power MOSFET is • -11.4 A, -60 V, $R_{DS(on)}$ = 175 m Ω (Max.) @ V_{GS} = -10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- $I_{D} = -5.7 \text{ A}$
- Low Gate Charge (Typ. 13 nC)
- Low Crss (Typ. 45 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

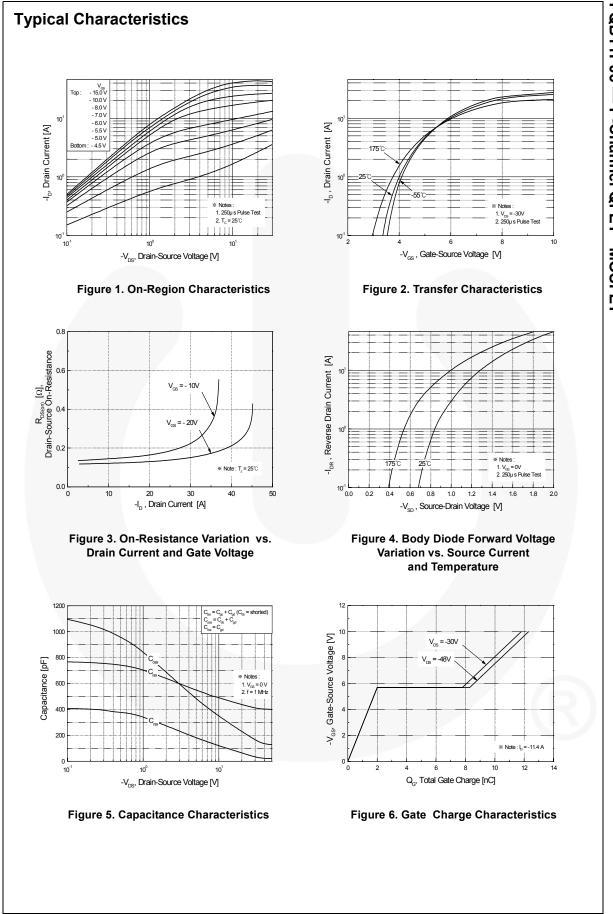
Symbol	Parameter		FQB11P06TM	Unit
V _{DSS}	Drain-Source Voltage		-60	V
ID	Drain Current - Continuous ($T_C = 25^{\circ}C$)		-11.4	А
	- Continuous (T _C = 100°C)		-8.05	A
I _{DM}	Drain Current - Pulsed	(Note 1)	-45.6	A
V _{GSS}	Gate-Source Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	160	mJ
I _{AR}	Avalanche Current	(Note 1)	-11.4	A
E _{AR}	Repetitive Avalanche Energy	(Note 1)	5.3	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-7.0	V/ns
P _D	Power Dissipation $(T_A = 25^{\circ}C)^*$		3.13	W
	Power Dissipation ($T_C = 25^{\circ}C$)		53	W
	- Derate above 25°C		0.35	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
TL	Maximum lead temperature for soldering, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

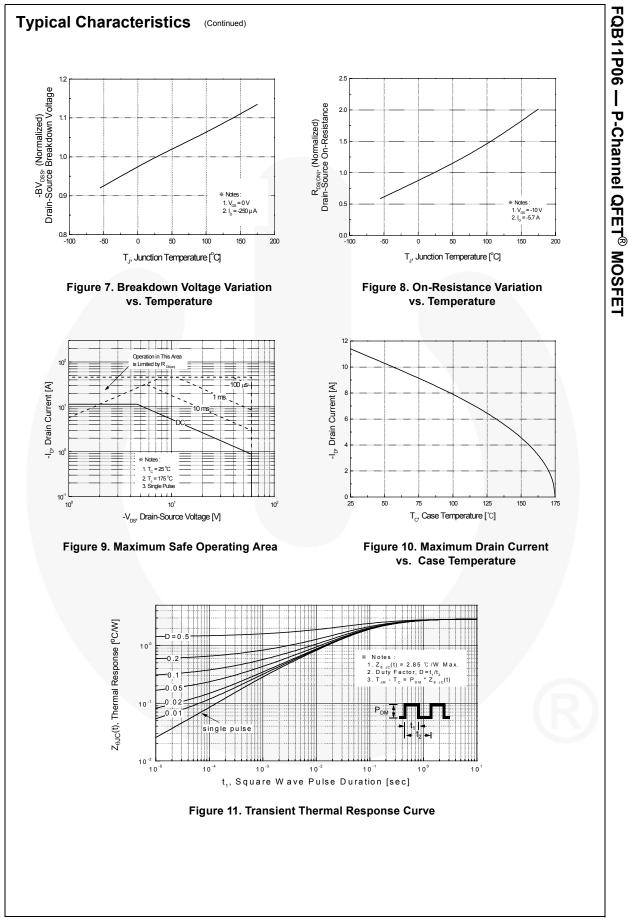
Symbol	Parameter	FQB11P06TM	Unit		
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max. 2.85				
R_{\thetaJA}	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	°C/W		
	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	40			

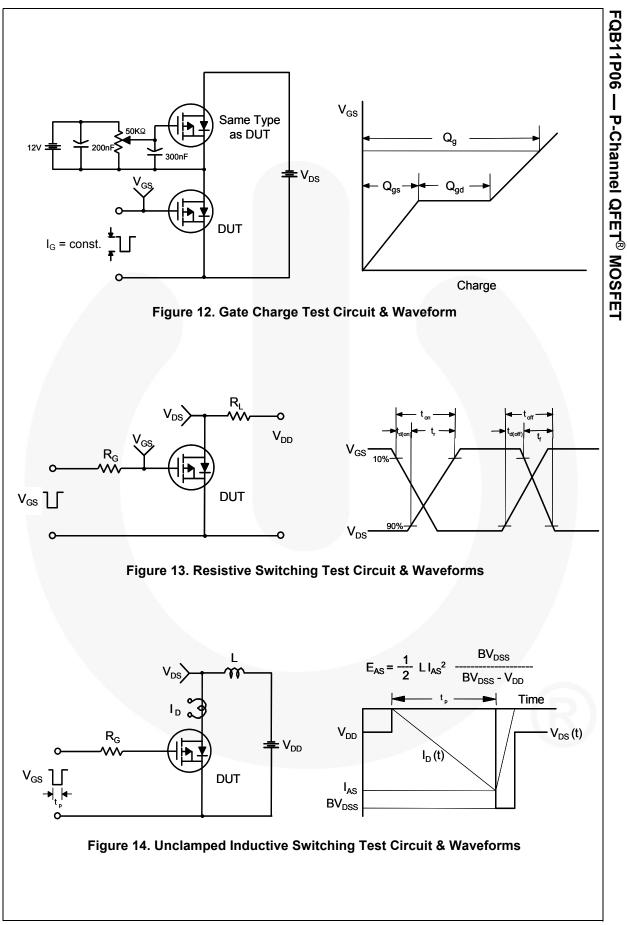
Part Number Top Mark Pacl			kage Packing Method Reel		Size	Tape Width		Quantity			
FQB1 ²			PAK Tape and Reel 330			mm 24 mm		n a	800 units		
	cal Cha	racteristics	T _C = 25°C	C unless ot	nerwise noted.				1		
Symbol		Parameter			Test Cond	litions		Min.	Тур.	Max.	Unit
Off Cha	aracterist	ics									
BV _{DSS}	Drain-Sou	rce Breakdown Volt	age	V _{GS} = 0 V, I _D = -250 μA			-60			V	
ΔΒV _{DSS} / ΔΤ _{.1}	Breakdow Coefficient	n Voltage Temperat	ure	I_D = -250 µA, Referenced to 25°C				-0.07		V/°C	
I _{DSS}	J		_	V _{DS} = -60 V, V _{GS} = 0 V					-1	μA	
·D22			$V_{DS} = -48 \text{ V}, \text{ T}_{C} = 150^{\circ}\text{C}$					-10	μΑ		
I _{GSSF}	Gate-Body Leakage Current, Forward			$V_{\rm DS} = -45 \text{ V}, V_{\rm C} = 150 \text{ C}$ $V_{\rm GS} = -25 \text{ V}, V_{\rm DS} = 0 \text{ V}$					-100	nA	
I _{GSSR}	,	Leakage Current,			25 V, V _{DS} =					100	nA
			_								
	racteristi		_	V -	V = 2	50 ·· A		2.0	1	10	V
V _{GS(th)}		shold Voltage	_	$V_{DS} = V_{GS}, I_D = -250 \mu A$		-2.0		-4.0	V		
R _{DS(on)}	Static Drain-Source On-Resistance		V _{GS} = -10 V, I _D = -5.7 A				0.14	0.175	Ω		
9 _{FS}	Forward T	ransconductance		V _{DS} =	-30 V, I _D = -	5.7 A			5.1		S
Dynami	ic Charac	teristics									
C _{iss}	Input Capa	acitance		V _{DS} = -25 V, V _{GS} = 0 V,				420	550	pF	
C _{oss}	Output Ca	pacitance			f = 1.0 MHz			195	250	pF	
C _{rss}	Reverse T	ransfer Capacitance	e						45	60	pF
Switchi		cteristics								1	
t _{d(on)}	Turn-On D	elay Time	_	V _{DD} =	-30 V, I _D = -	5.7 A,			6.5	25	ns
t _r	Turn-On R	ise Time		$R_G = 2$	-				40	90	ns
t _{d(off)}	Turn-Off D	,	_				() - t- ()		15	40	ns
t _f	Turn-Off F	all Time					(Note 4)		45	100	ns
Qg	Total Gate	Charge		$V_{DS} =$	-48 V, I _D = -	11.4 A,			13	17	nC
Q _{gs}	Gate-Sour			V _{GS} = -10 V (Note 4)			2.0		nC		
Q _{gd}	Gate-Drair	n Charge					(Note 4)		6.3		nC
Drain-S	ource Di	ode Characteri	istics ar	nd Max	cimum Ra	tings					
I _S	Maximum Continuous Drain-Source Dic								-11.4	Α	
I _{SM}	Maximum Pulsed Drain-Source Diode F								-45.6		
V _{SD}		rce Diode Forward		V _{GS} = 0 V, I _S = -11.4 A					-4.0	V	
t _{rr}		ecovery Time	0 -	$V_{GS} = 0 V, I_S = -11.4 A,$				83		ns	
	Reverse Recovery Charge			$dI_{\rm F} / dt = 100 \text{ A}/\mu \text{s}$							

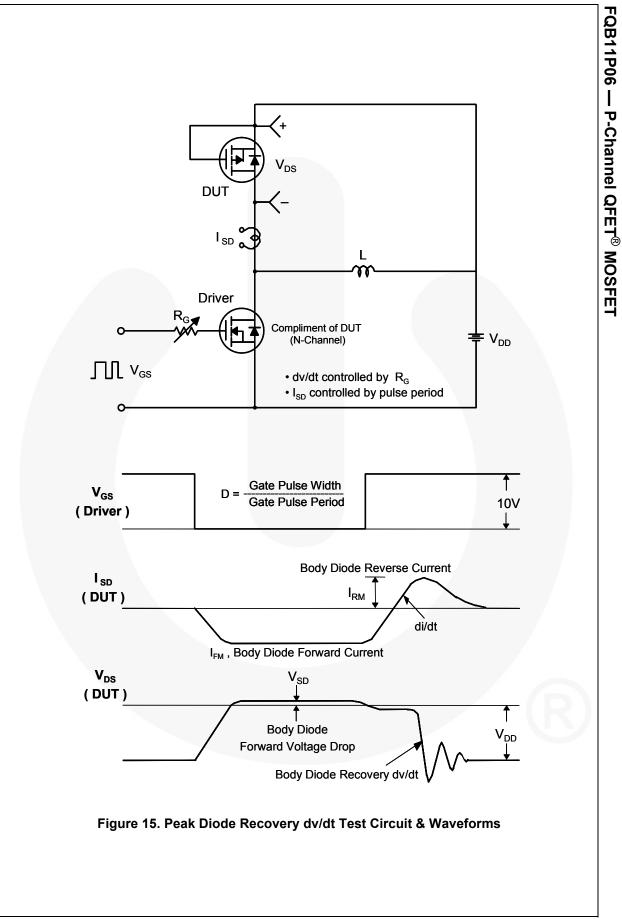
Notes: 1. Repetitive rating : pulse-width limited by maximum junction temperature. 2. L = 1.44 mH, $I_{AS} = -11.4$ A, $V_{DD} = -25$ V, $R_G = 25 \Omega$, starting $T_J = 25^{\circ}$ C. 3. $I_{SD} \le -11.4$ A, di/dt ≤ 300 A/µs, $V_{DD} \le BV_{DSS}$, starting $T_J = 25^{\circ}$ C. 4. Essentially independent of operating temperature



FQB11P06 — P-Channel QFET[®] MOSFET







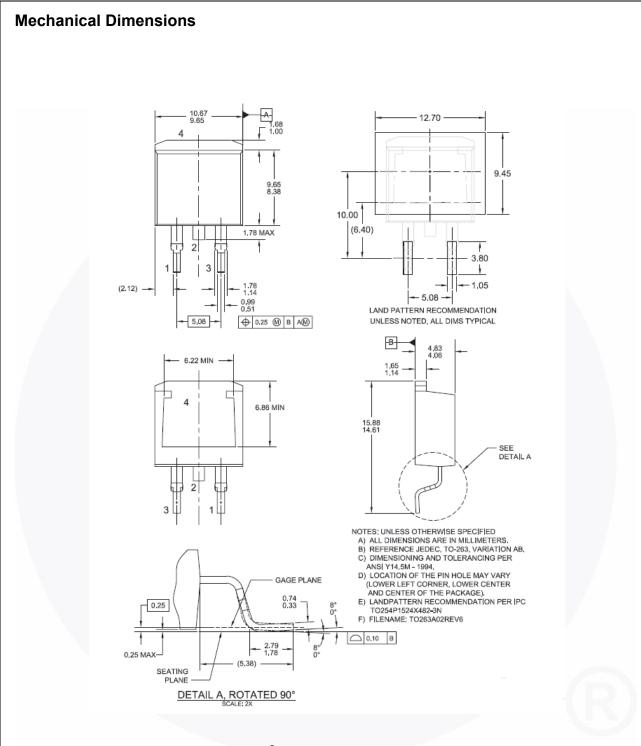


Figure 16. TO263 (D²PAK), Molded, 2-Lead, Surface Mount

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FQB11P06

- P-Channel QFET[®] MOSFET



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No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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